Amendments to the Specification:

Please replace the paragraph beginning at page 1, line 3, with the following rewritten paragraph:

BACKGROUND OF THE ~~INVENTION~~ DISCLOSURE

Please replace the paragraph beginning at page 1, line 9, with the following rewritten paragraph:

1. Field of the ~~Invention~~ Disclosure

Please replace the paragraph beginning at page 1, line 10, with the following rewritten paragraph:

The present ~~invention~~ disclosure relates to a semiconductor laser device, and more particularly, to a laser device having a smooth cleavage plane.

Please replace the paragraph beginning at page 4, line 14, with the following rewritten paragraph:

SUMMARY OF THE ~~INVENTION~~ DISCLOSURE

Please replace the paragraph beginning at page 4, line 15, with the following rewritten paragraph:

The present ~~invention~~ disclosure provides a laser device having an excellent laser exiting surface and a method of manufacturing the same.

Please replace the paragraph beginning at page 4, line 17, with the following rewritten paragraph:

The present ~~invention~~ disclosure also provides a semiconductor laser device having a low operating current and an improved laser oscillation efficiency, and a method of manufacturing the same.

Please replace the paragraph beginning at page 4, line 20, with the following rewritten paragraph:

According to an aspect of the present ~~invention~~ disclosure, there [[is]] may be

provided a semiconductor laser device, which includes a multi-semiconductor material layered mesa structure having a laser resonance layer on a substrate and cladding layers formed above and below the resonance layer, comprising a current injection ridge and force distribution ridges at the both sides of the current injection ridge formed on an upper portion of the mesa structure and protruding from the surface of an upper surface of the mesa structure.

Please replace the paragraph beginning at page 4, line 27, with the following rewritten paragraph:

According to another aspect of the present ~~invention~~ disclosure, there [[is]] may be provided a semiconductor laser device, which includes a multi-semiconductor material layered mesa structure having a laser resonance layer on a substrate and cladding layers formed above and below the resonance layer, comprising rounded corners connected to the substrate, in a lower portion of the mesa structure, and a current injection ridge and force distribution ridges formed in an upper portion of the mesa structure and protruding from an upper surface of the mesa structure.

Please replace the paragraph beginning at page 5, line 25, with the following rewritten paragraph:

The above aspects and advantages of the present ~~invention~~ disclosure will ~~become more apparent by describing in detail a preferred embodiment~~ be described in detailed exemplary embodiments thereof with reference to the attached drawings in which:

Please replace the paragraph beginning at page 6, line 13, with the following rewritten paragraph:

DETAILED DESCRIPTION OF ~~THE INVENTION~~ PREFERRED EMBODIMENTS

Please replace the paragraph beginning at page 8, line 29, with the following rewritten paragraph:

According to the embodiments of the present ~~invention~~ disclosure, rounded corners are formed in lower portions of a mesa structure, and force distribution ridges are disposed adjacent to a current injection ridge in an upper portion of the mesa structure. Accordingly, a smooth cleavage plane perpendicular to the oscillation surface is obtained by scribing, with a high yield. Because of the smooth cleavage plane, the laser oscillation efficiency is improved and the operating current of the laser device is lowered. The force distribution ridge may also distribute a load applied to the current injection ridge when bonding flip chips.